

ABSTRACT OF THE DISCLOSURE

Disclosed is a semiconductor device comprising a semiconductor substrate, a capacitor provided above the semiconductor substrate and including a bottom electrode, a top electrode, and a dielectric film provided between the top electrode and the bottom electrode, an insulating region surrounding the capacitor and having a first hole which extends in a vertical direction and reaches the top electrode and a second hole which extends in the vertical direction and is spaced away from the capacitor, and a first wiring connected to the top electrode and including a first conductive portion formed in the first hole and a second conductive portion formed in the second hole, the first wiring having a barrier metal film between the insulating region and the first conductive portion and having no barrier metal film between the insulating region and the second conductive portion.